

図 1

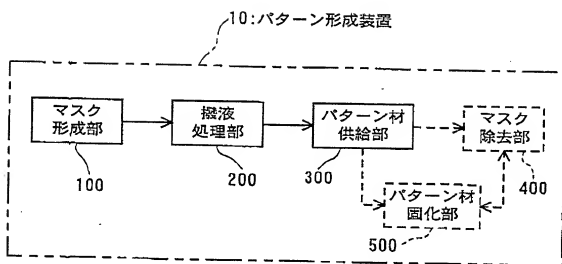


图 2

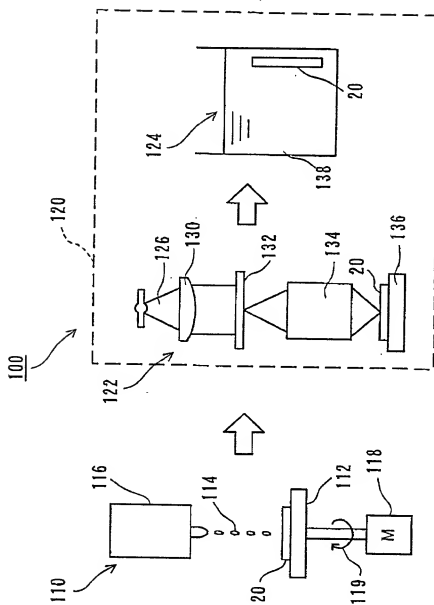


図 3

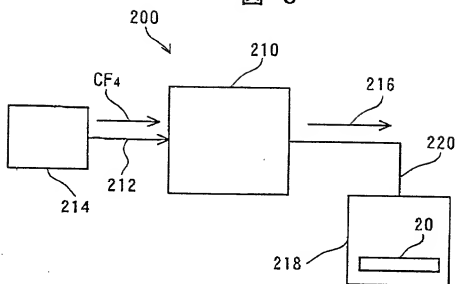


图 4

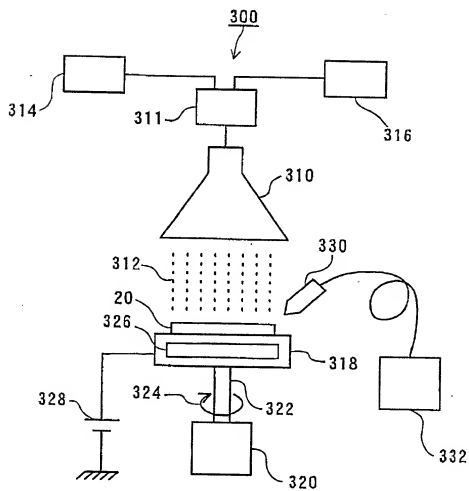


図 5

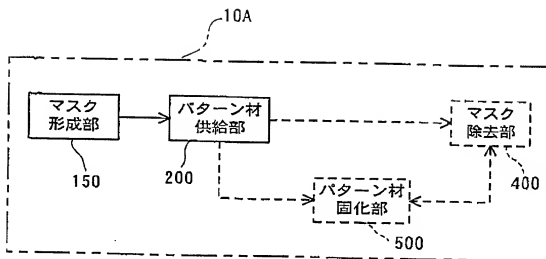


Figure 6 is a schematic diagram of a system 150. The system includes a main chamber 152 containing a component 24. A fluid inlet 154 enters the chamber from the bottom, and a fluid outlet 158 exits from the top. The chamber is connected to a pump 160 via a line 162. A valve 164 is located on the line between the chamber and the pump. A fluid reservoir 170 is connected to the main chamber 152 via a line 172. The reservoir contains a coil 174. A valve 166 is located on the line between the reservoir and the main chamber. A fluid source 178 is connected to the main chamber 152 via a line 176 and a valve 175. A dashed line 180 connects the main chamber 152 to a dashed box 184. A valve 182 is located on the dashed line 180.

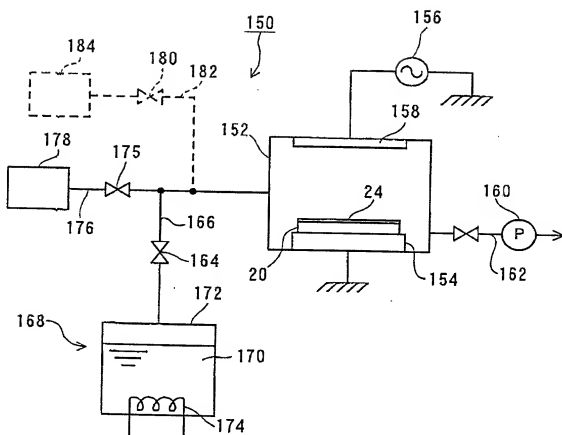


図 7

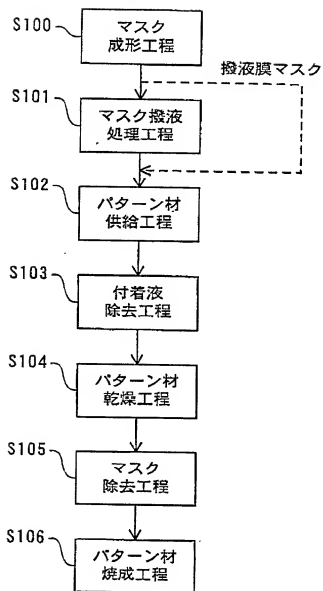


図 8

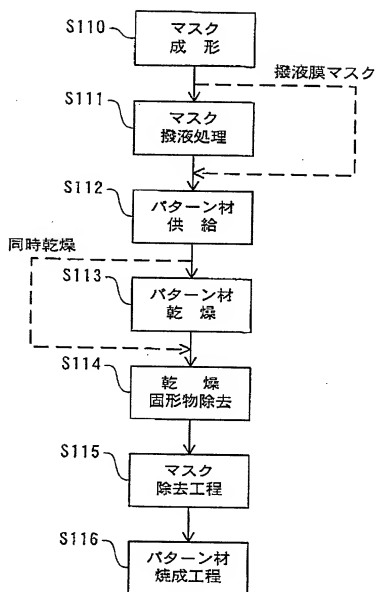


图 9

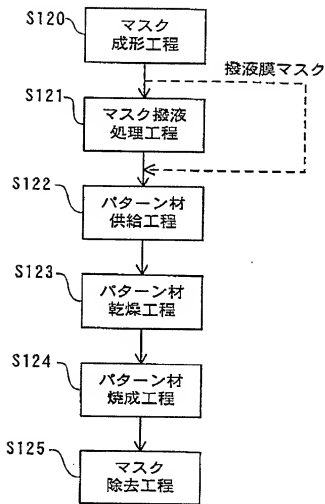


図 10

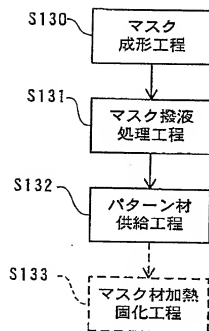


図 11

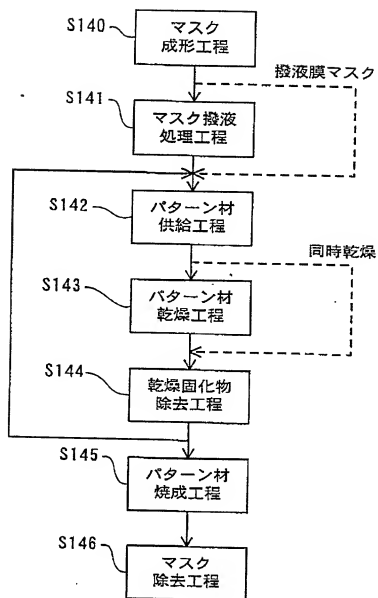


図 12

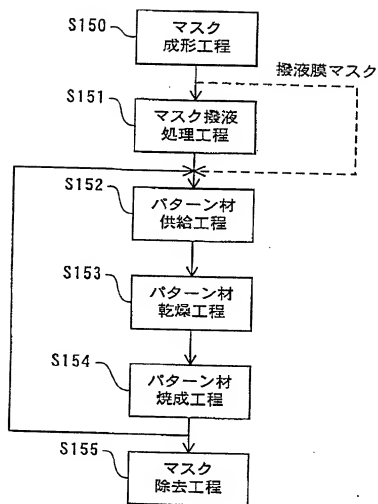


図 13

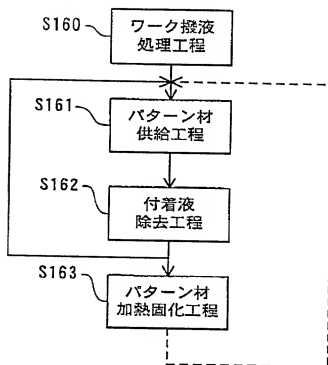


図 14

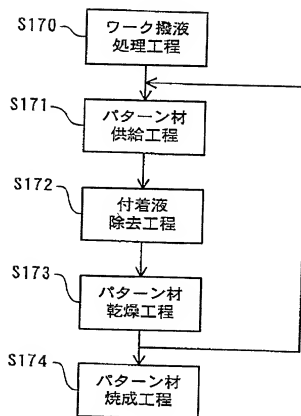


図 15

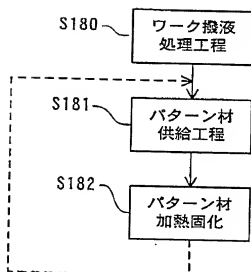


図 16

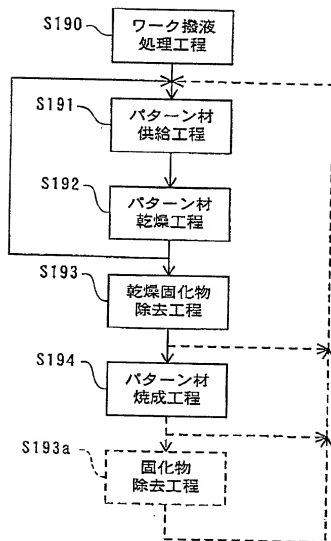


図 17

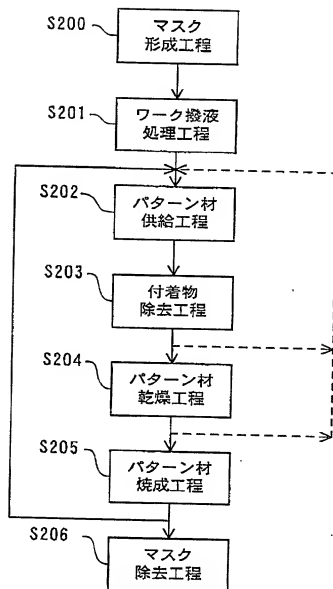
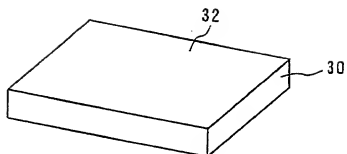
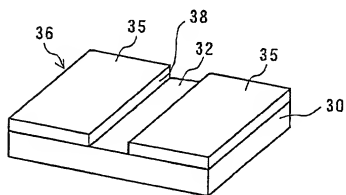


图 18

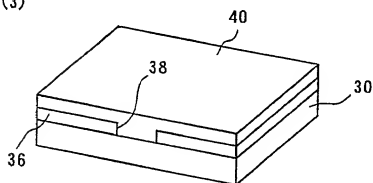
(1)



(2)

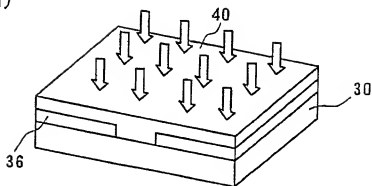


(3)

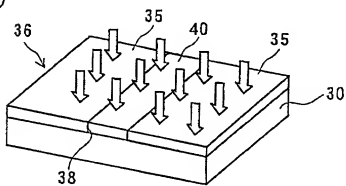


19

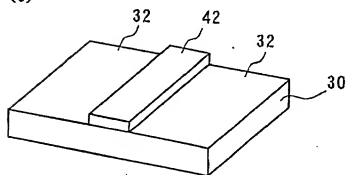
(1)

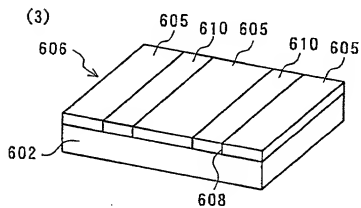
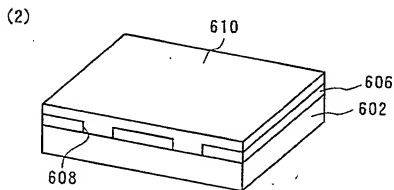
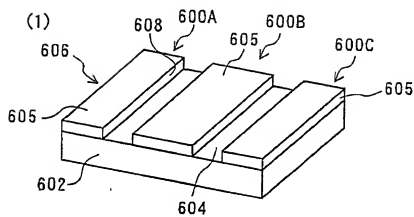


(2)

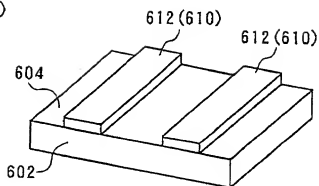


(3)

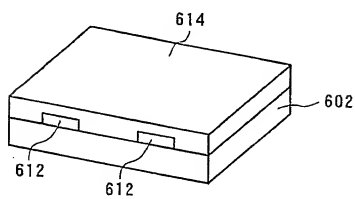




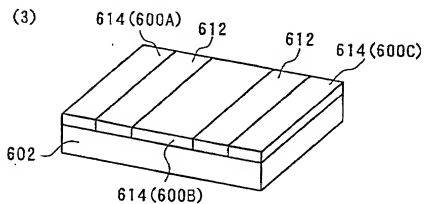
(1)



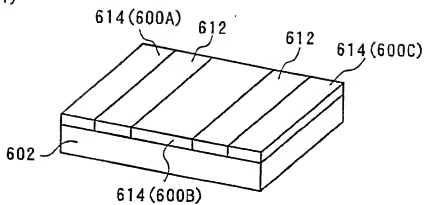
(2)



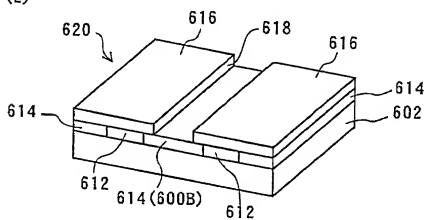
(3)



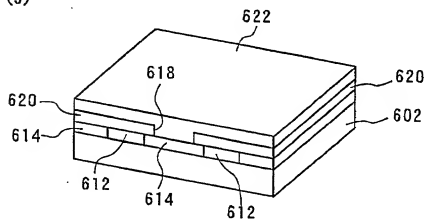
(1)



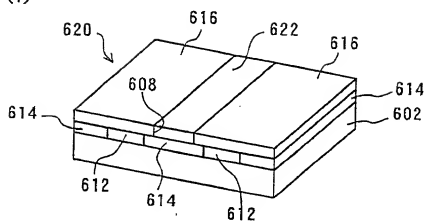
(2)



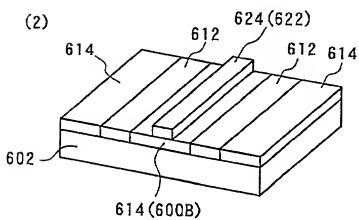
(3)

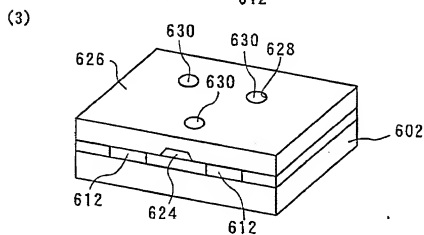
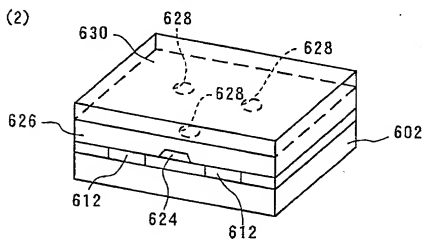
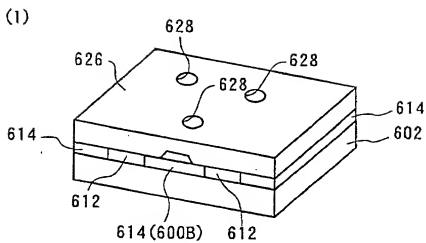


(1)

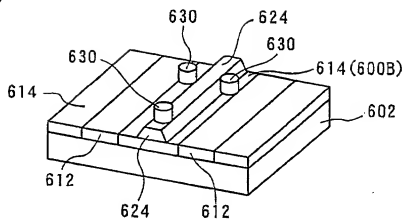


(2)

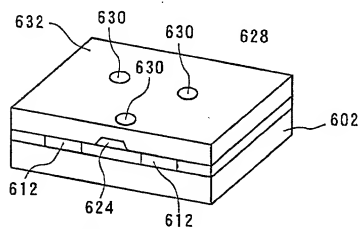




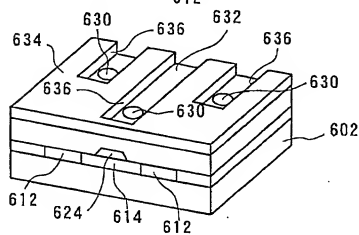
(1)

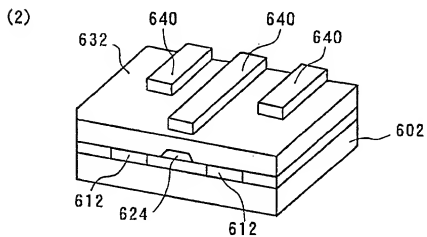
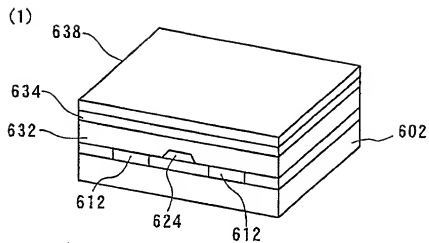


(2)



(3)





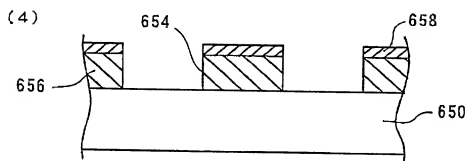
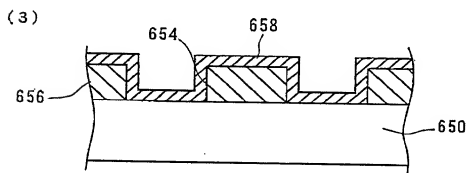
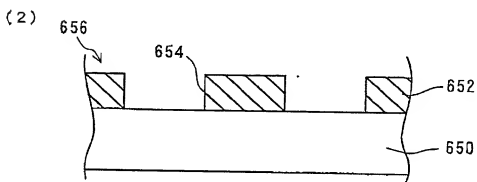
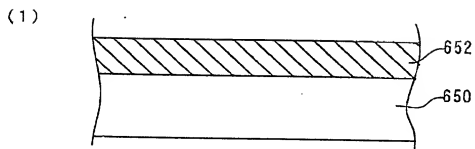


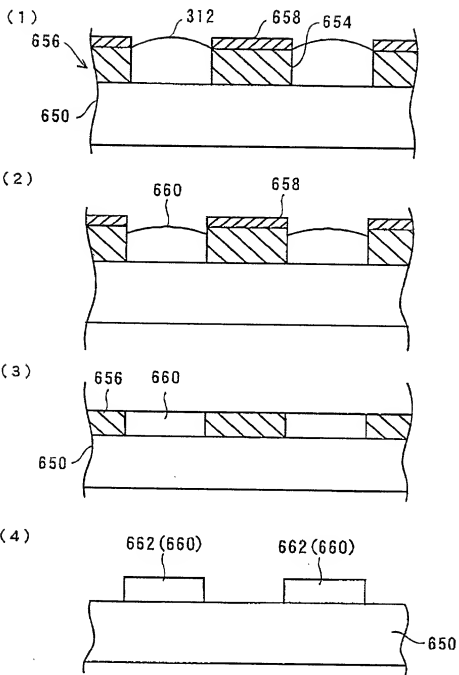
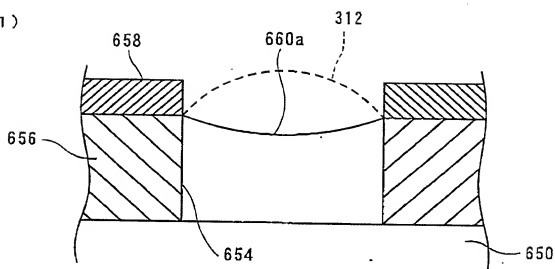
Figure 28 is a cross-sectional diagram of a semiconductor device, showing four stages of construction labeled (1) through (4).
 Stage (1) shows a substrate 650 with a patterned layer 656 on top. The layer 656 has three rectangular regions. The central region is labeled 312, and the two side regions are labeled 658 and 654. The top surface of the central region 312 is curved.
 Stage (2) shows the same substrate 650 with a patterned layer 660 on top. The layer 660 has three rectangular regions. The central region is labeled 660, and the two side regions are labeled 658. The top surface of the central region 660 is curved.
 Stage (3) shows the same substrate 650 with a patterned layer 656 on top. The layer 656 has three rectangular regions. The central region is labeled 660, and the two side regions are labeled 656. The top surface of the central region 660 is curved.
 Stage (4) shows the same substrate 650 with two rectangular regions on top, both labeled 662 (660). The top surface of these regions is flat.


図 29

(1)



(2)

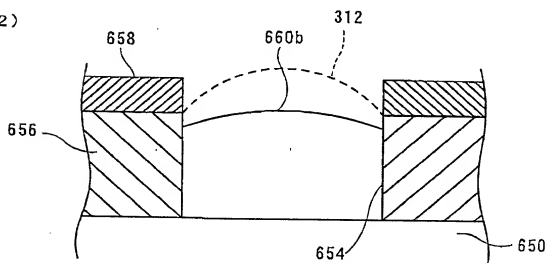


图 30

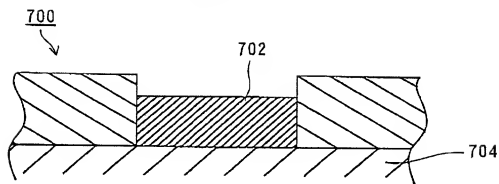


图 31

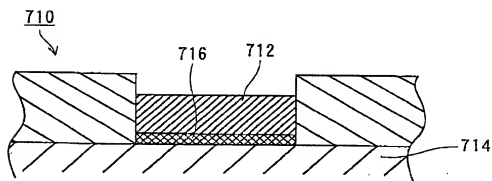
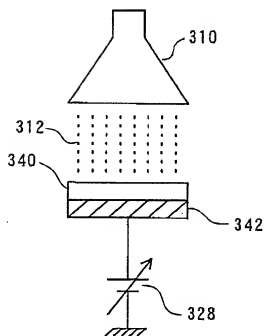
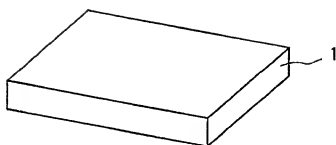


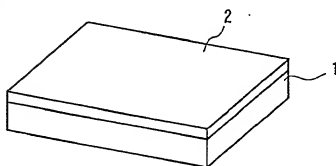
图 32



(1)



(2)



(3)

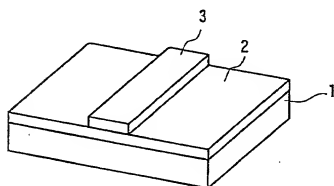


图 34

